

LH03 Series of Products interconvert:

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2SK30A

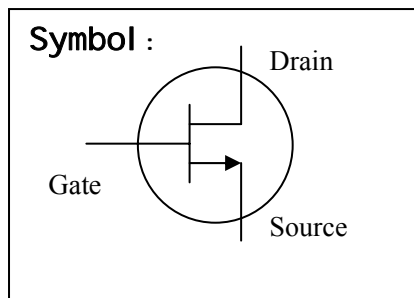
Silicon N-Channel Junction FET

Application:

For charge sensor, meter amplifier circuit, rheostat, chopper and gain controller for AGC, electronic switch.

Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Ratings	Unit
Gate to Drain voltage	V _{GD0}	-50	V
Gate to Source voltage	V _{GSO}	-50	V
Gate current	I _G	10	mA
Allowable power dissipation	P _D	250	mW
Junction Temperature	T _j	125	°C
Storage Temperature	T _{stg}	-55 to +125	°C



Package example:

Package	D	S	G
SC-59			
SOT-23			
TO-92S			
* TO-92	3	1	2
TO-18			

Electrical Characteristics (Ta=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source cut-off current	I _{DSS}	V _{DS} = 10V, V _{GS} = 0V	0.3		6.5	mA
Gate to Source leakage current	I _{GSS}	V _{GS} = -30V, V _{DS} = 0V			-1.0	nA
Gate to Drain voltage	V _{GDS}	I _G = -100μA, V _{DS} = 0V	-50			V
Gate to Source cut-off voltage	V _{GS(OFF)}	V _{DS} = 10V, I _D = 0.1μA	-0.4		-5.0	V
Forward transfer admittance	Y _{fs}	V _{DS} = 10V, V _{GS} = 0V, f = 1KHZ	1.2			mS
Input capacitance (Common Source)	C _{iss}	V _{DS} = 10V, V _{GS} = 0V, f = 1MHZ		8.2		pF
Reverse transfer capacitance (Common Source)	C _{rss}			2.6		pF

I_{DSS} Rank Classification

Rank	R	O	Y	GR
I _{DSS} (mA)	0.3 to 0.75	0.6 to 1.4	1.2 to 3.0	2.6 to 6.5
Marking Symbol	035D	035E	035F	035G

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